

Title (en)

ELECTRONIC STRUCTURE INCLUDING AN EPITAXIAL LAYER ON SINTERED SILICON

Title (de)

ELEKTRONISCHE STRUKTUR MIT EINER EPITAXIALSCHICHT AUF GESINTERTEM SILICIUM

Title (fr)

STRUCTURE ELECTRONIQUE A COUCHE EPITAXIEE SUR SILICIUM FRITTE

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Application

**EP 10723184 A 20100401**

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Abstract (en)

[origin: WO2010112782A2] The invention relates to a method and an electronic structure (35) including a substrate (26, 28), produced by sintering silicon powders, and at least one epitaxial layer (32). The invention also relates to photovoltaic cells and can be used in other fields, such as the fields of electronics, microelectronics or optoelectronics.

IPC 8 full level

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